Compound Semiconductor Materials Europe TC Chapter
Meeting Summary and Minutes

April 14th, 2026
04:00 PM – 06:00 PM CEST
Online

TC Chapter Announcements

Next TC Chapter Meeting
November 10-13, 2026, SEMICON Europa. Check www.semi.org/en/standards for the latest update.

Table 1 Meeting Attendees

Co-Chair: Arnd Weber (SiCrystal), Christian Kranert (Fraunhofer IISB)
SEMI Staff: Kevin Nguyen (SEMI)

Company	*Last*	*First*
Wolfspeed	*Barbieri*	*Tom*
Scientic Visual	*Cheze*	*Caroline*
Infineon Technologies Austria AG	*Fey*	*Julian*
Lasertec	*Fujiki*	*Shota*
Crystal IS	*Grandusky*	*James*
KLA	*Kallus*	*Dave*
Kushan Kinglai Hygienic Materials	*Kingson*	*Austin*
Kitabatake	*Kitabatake*	*Kitabatake*
Fraunhofer IISB	*Kranert*	*Christian*
Bruker	*Lafford*	*Tamzin*
Wolfspeed	*Rao*	*Shailaja*
SiCrystal	*Weber*	*Arnd*
SICC	*Yang*	*Shixing*

Italic indicates online participant. Bold indicates in-person attendance.

Table 2 Leadership Changes

WG/TF/SC/TC Name	*Previous Leader*	*New Leader*
None		

Table 3 Committee Structure Changes

Previous WG/TF/SC Name	*New WG/TF/SC Name or Status Change*
None	

Table 4 Ballot Results

Document #	*Document Title*	*Committee Action*
7111	Revision of SEMI M81-0418, Guide for Defects Found in Monocrystalline Silicon Carbide Substrates	**Passed** with editorial changes
7416	Reapproval of SEMI M82-0820 Test Method for the Carbon Acceptor Concentration In Semi-Insulating Gallium Arsenide Single Crystals by Infrared Absorption Spectroscopy	**Passed** as balloted

Note 1: **Passed** ballots and line items will be submitted to the ISC Audit & Review Subcommittee for procedural review.

Note 2: **Failed** ballots and line items were returned to the originating task forces for re-work and re-balloting or abandoning.

Table 5 Ratification Ballot Results

Document #	*Document Title*	*ISC A&R Action*	*A&R Forms*
None			

Note 1: **Passed** Ratification ballots will be submitted to SEMI publication for final processing.

Note 2: **Failed** Ratification ballots were returned to the originating task forces for re-work and re-balloting or abandoning.

Table 6 Authorized Activity

#	*Type*	*SC/TF/WG*	*Details*
None			

#1 SNARFs and TFOFs are available for review on the SEMI web site at: http://downloads.semi.org/web/wstdsbal.nsf/tfofsnarf

Table 7 Authorized Ballots

#	*When*	*TF*	*Details*
None			

Table 8 New Action Items

Item #	*Assigned to*	*Details*
041626-1	Kevin Nguyen (SEMI Staff)	To send James Grandusky (Crystal IS) a blank TFOF for AlN Wafers Task Force

Table 9 Previous Meeting Action Items

Item #	*Assigned to*	*Details*	*Status*
None			

1 Welcome, Reminders, and Introductions

1.1 Arnd Weber called the meeting to order at 04:00 PM. Attendees introduced themselves. Kevin Nguyen presented meeting reminders on antitrust, intellectual property issues and effective meeting guidelines.

2 Review of Previous Meeting Minutes

2.1 The TC Chapter reviewed the minutes of the previous meeting.

Motion:	To approve the meeting minutes
By / 2nd:	By: Christian Kranert / Fraunhofer IISB Second: Tom Barbieri / Wolfspeed
Discussion:	None
Vote:	5-0. Motion passed.

3 Task Force Reports

3.1 *SiC-Task Force*

3.1.1 Arnd Weber reported the TF will have a kick-off meeting for revision of SEMI M55-0921, Specification for Polished Monocrystalline Silicon Carbide Wafers in May, 2026. If anyone is interested, please contact Arnd.

3.2 *5-year Review Task Force*

3.2.1 No report.

3.3 *Test Methods Task Force*

3.3.1 Christian Kranert reported no activity. However, it may be active when the 5 year review cycle is up for

- SEMI M91-0622 - Test Method for Determination of Threading Screw Dislocation Density in 4H-SIC by X-Ray Topography, and
- SEMI M93-0624 - Test Method for Quantifying Basal Plane Dislocation Density in 4H-SiC by X-Ray Diffraction Topography/Imaging.

3.4 *SIC Epi-Defects Task Force*

3.4.1 Christian Kranert reported on the progress made regarding Document 7160, New Standard: Guide for Defects Found in Homoepitaxial Layers of Silicon Carbide. However, it takes more time than anticipated.

3.5 *Silicon Carbide Engineered Substrate Task Force*

3.5.1 No report.

4 Ballot Review

4.1 Doc. 7111, Revision of SEMI M81-0418, Guide for Defects Found in Monocrystalline Silicon Carbide Substrates

4.1.1 Passed with editorial changes. Refer to attachment for details.

Attachment: 7111 A&R rev1

Attachment: M81_7111_Ballot_review_1-26

4.2 Doc. 7416, Reapproval of SEMI M82-0820, Test Method for the Carbon Acceptor Concentration In Semi-Insulating Gallium Arsenide Single Crystals by Infrared Absorption Spectroscopy

4.2.1 Passed as balloted. Refer to attachment for details.

Attachment: 7416 A&R rev1

5 Liaison Reports

5.1 *NA CSM TC Chapter*

5.1.1 Kevin Nguyen reported the TC Chapter has not been meeting for a while.

5.2 *China CSM TC Chapter*

5.2.1 Kevin Nguyen reported. Of note:

- Last meeting
    - Oct 22, 2025
- Next meeting
    - TBD
- Authorized Activities
    - Doc. 7407, New Standard: Test method for determining net carrier density profiles in silicon carbide epitaxial wafers by capacitance-voltage measurements with a mercury probe
    - Doc. 7408, New Standard: Specification For Bonding Silicon Carbide Homoepitaxial Wafer
- Abolished SNARFs
    - Doc. 6767, New Standard: Test Method for GBIR, SBIR, GF3R, SFQR and SORI of Silicon Carbide Wafers by Oblique Incident Interference Method
    - Doc. 6768, New Standard: Test Method for Residual Stress of Silicon Carbide Wafers by Photoelastic Effect

Attachment: CSM China TC Chapter Dec 2025

5.3 *Japan CSM TC Chapter*

5.3.1 Kevin Nguyen reported. Of note:

- Last meeting
    - Thursday, December 18, 2025
    - SEMICON Japan 2025
- Next meeting
    - TBD
- New TF
    - SiC Material and Wafer TF
        - Charter: The TF addresses specifications and test methods of SiC wafers including homoepitaxial wafers and engineered substrates.

- Scope: The TF will develop and maintain SEMI Standards relating to and directly concerning SiC wafers including homoepitaxial wafers and engineered substrates. These include, but are not limited to:
    - specific standards addressing the geometrical and mechanical parameters, e.g., diameter, thickness, edge contour, etc.
    - test methods including test equipment, evaluation methods, etc.

Attachment: CSM_JA TC Chapter Liaison Report_April 2026_R0

6 New Business

6.1 SNARF for New Standard: Specification for Polished Monocrystalline AlN Wafers

6.1.1 James Grandusky (Crystal IS) presented a proposal for New Standard: Specification for Polished Monocrystalline AlN Wafers. The specification will be similar to that of silicon carbide. The TFOF was not submitted, so this proposal will be approved by the Global Coordinating Subcommittee (GCS). Action Item – Kevin will send a blank TFOF to James.

Attachment: SNARF_April2026 AlN

7 Next Meeting and Adjournment

7.1 The next meeting is scheduled for November, 2026 in conjunction with SEMICON Europa in Munich, Germany. Refer to http://www.semi.org/standards for the latest update.

Having no further business, adjournment was at 6:00 PM CEST.

Respectfully submitted by:

Kevin Nguyen,
SEMI Standards Operations Manager
Phone: 408-943-7997
Email: knguyen@semi.org

Minutes tentatively approved by:

Arnd Weber (SiCrystal)	
Christian Kranert (Fraunhofer IISB)	

Table 10 Index of Available Attachments#1

Title
7111 A&R rev1
M81_7111_Ballot_review_1-26
7416 A&R rev1
CSM China TC Chapter Dec 2025
CSM_JA TC Chapter Liaison Report_April 2026_R0
SNARF_April2026 AlN

#1 Due to file size and delivery issues, attachments must be downloaded separately. A .zip file containing all attachments for these minutes is available at www.semi.org. For additional information or to obtain individual attachments, please contact [SEMI Staff Name] at the contact information above.